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Claims:-

1. A method of sensing the concentration of an oxidising gas in a gas mixture using a semiconductor gas sensor having a resistivity sensitive to the oxidising gas, which comprises increasing the sensor operating temperature to a first temperature to allow the sensor surface to reset then decreasing the sensor operating temperature to a second temperature and analysing the resultant resistance of the sensor at the second temperature.

2. A method according to claim 1 in which the first temperature is 400 to 800°C and the second temperature is 200 to 500°C.

3. A method according to claim 1 or 2 wherein the sensor resistance is analyzed as a function of time.

4. A method according to any preceding claim in which the oxidising gas is NO_2, NO, Cl_2, or O_3.

5. A method according to any preceding claim in which the sensor is a layer of WO_3, In_2O_3, MoO_3 or SnO_2.

6. A method according to claim 5 wherein the sensor is a layer of WO_3 and the oxidising gas is O_3.

AMENDED SHEET